

PHASE CONTROL SCR



$V_T < 1.45V @ 40A$
 $I_{TSM} = 500A$
 $V_{RRM} = 800 \text{ to } 1600V$

Description/Features

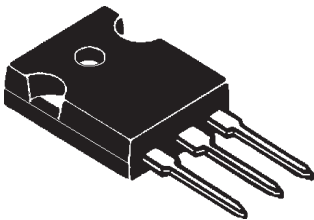
The 40TPS... **SAFEIR** series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125°C junction temperature. Low lgt parts available.

Typical applications are in input rectification (soft start) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.

Major Ratings and Characteristics

Characteristics	40TPS..	Units
$I_{T(AV)}$ Sinusoidal waveform	35	A
I_{RMS}	55	A
V_{RRM}/V_{DRM}	upto1600	V
I_{TSM}	500	A
$V_T @ 40A, T_J = 25^\circ C$	1.45	V
dv/dt	1000	V/ μs
di/dt	100	A/ μs
T_J	-40 to 125	°C

Package Outline



TO-247AC

Voltage Ratings

Part Number	V_{RRM}/V_{DRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non repetitive peak reverse voltage V	I_{RRM}/I_{DRM} 125°C mA
40TPS08	800	900	10
40TPS12	1200	1300	
40TPS16	1600	1700	

Absolute Maximum Ratings

Parameters		40TPS..	Units	Conditions		
I _{T(AV)}	Max. Average On-state Current	35	A	@ T _C = 79° C, 180° conduction half sine wave		
I _{T(RMS)}	Max. Continuous RMS On-state Current As AC switch	55				
I _{TSM}	Max. Peak One Cycle Non-Repetitive Surge Current	500	A	10ms Sine pulse, rated V _{RRM} applied	Initial T _J = T _J max.	
		600		10ms Sine pulse, no voltage reapplied		
I ² t	Max. I ² t for Fusing	1250	A ² s	10ms Sine pulse, rated V _{RRM} applied		
		1760		10ms Sine pulse, no voltage reapplied		
I ² √t	Max. I ² √t for Fusing	12500	A ² √s	t = 0.1 to 10ms, no voltage reapplied		
V _{T(TO)1}	Low Level Value of Threshold Voltage	1.02	V	T _J = 125°C		
V _{T(TO)2}	High Level Value of Threshold Voltage	1.23				
r _{t1}	Low Level Value of On-state Slope Resistance	9.74				
r _{t2}	High Level Value of On-state Slope Resistance	7.50	mΩ			
V _{TM}	Max. Peak On-state Voltage	1.85	V	@ 110A, T _J = 25°C		
di/dt	Max. Rate of Rise of Turned-on Current	100	A/μs	T _J = 25°C		
I _H	Max. Holding Current	100	mA			
I _L	Max. Latching Current	200				
I _{RRM} /	Max. Reverse and Direct	0.5		T _J = 25°C	V _R = rated V _{RRM} /V _{DRM}	
I _{DRM}	Leakage Current	10		T _J = 125°C		
dv/dt	Max. Rate of Rise of Off-state Voltage	40TPS08	V/μs	T _J = T _J max., linear to 80% V _{DRM} , R _g -k = open		
		40TPS12/16				1000

Triggering

Parameters		40TPS..	Units	Conditions	
P _{GM}	Max. peak Gate Power	10	W		
P _{G(AV)}	Max. average Gate Power	2.5			
I _{GM}	Max. peak Gate Current	2.5	A		
- V _{GM}	Max. peak negative Gate Voltage	10	V		
V _{GT}	Max. required DC Gate Voltage to trigger	4.0		T _J = - 40°C	Anode supply = 6V resistive load
		2.5		T _J = 25°C	
		1.7		T _J = 125°C	
I _{GT}	Max. required DC Gate Current to trigger	270	mA	T _J = - 40°C	
		150		T _J = 25°C	
		80		T _J = 125°C	
		40		T _J = 25°C, for 40TPS08A	
V _{GD}	Max. DC Gate Voltage not to trigger	0.25	V	T _J = 125°C, V _{DRM} = rated value	
I _{GD}	Max. DC Gate Current not to trigger	6	mA		

Thermal-Mechanical Specifications

Parameters			40TPS..	Units	Conditions
T _J	Max. Junction Temperature Range		- 40 to 125	°C	
T _{stg}	Max. Storage Temperature Range		- 40 to 125		
R _{thJC}	Max. Thermal Resistance Junction to Case		0.6	°C/W	DC operation
R _{thJA}	Max. Thermal Resistance Junction to Ambient		40		
R _{thCS}	Max. Thermal Resistance Case to Heatsink		0.2		Mounting surface, smooth and greased
wt	Approximate Weight		6 (0.21)	g (oz.)	
T	Mounting Torque	Min.	6 (5)	Kg-cm (lbf-in)	
		Max.	12 (10)		
Case Style			TO-247AC		

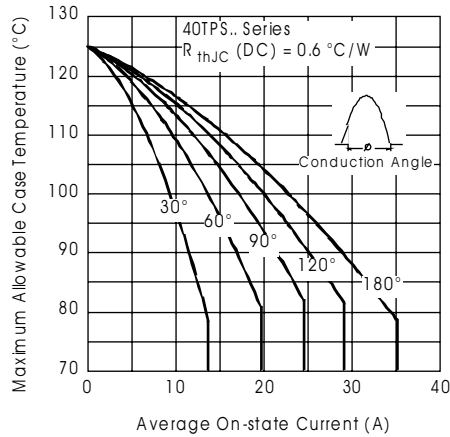


Fig. 1 - Current Rating Characteristics

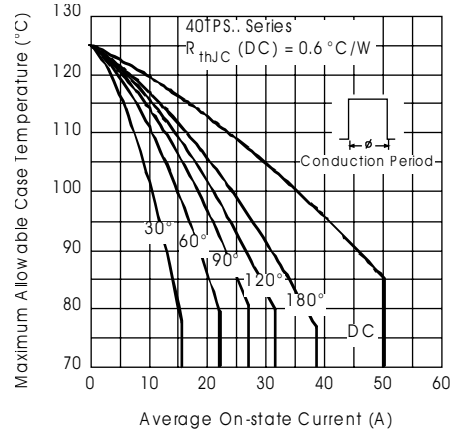


Fig. 2 - Current Rating Characteristics

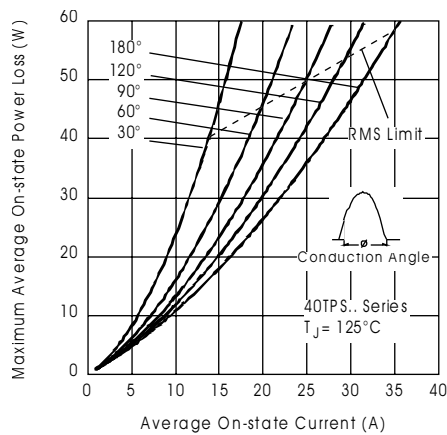


Fig. 3 - On-state Power Loss Characteristics

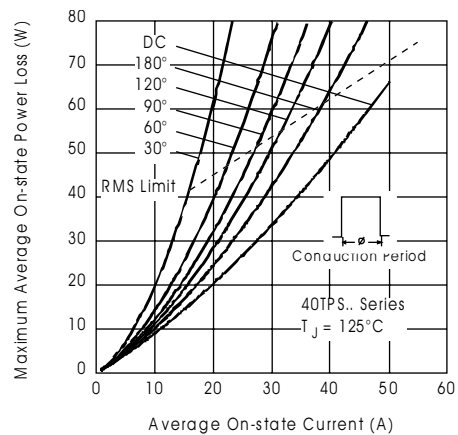


Fig. 4 - On-state Power Loss Characteristics

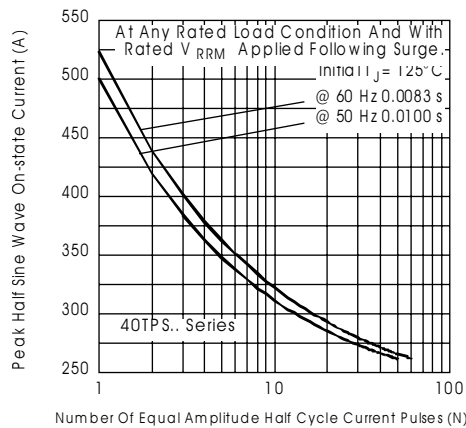


Fig. 5 - Maximum Non-Repetitive Surge Current

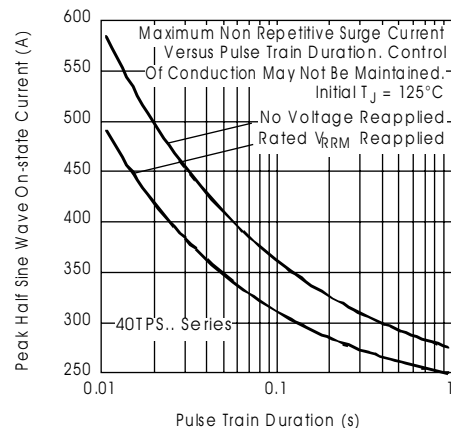


Fig. 6 - Maximum Non-Repetitive Surge Current

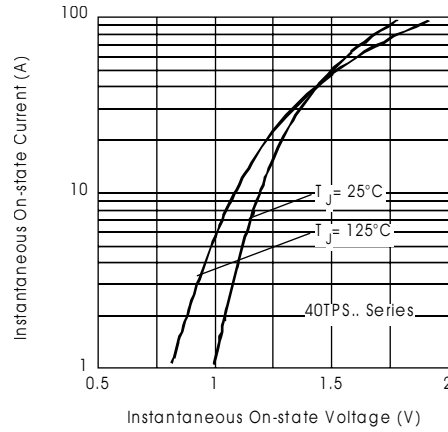


Fig. 7 - On-state Voltage Drop Characteristics

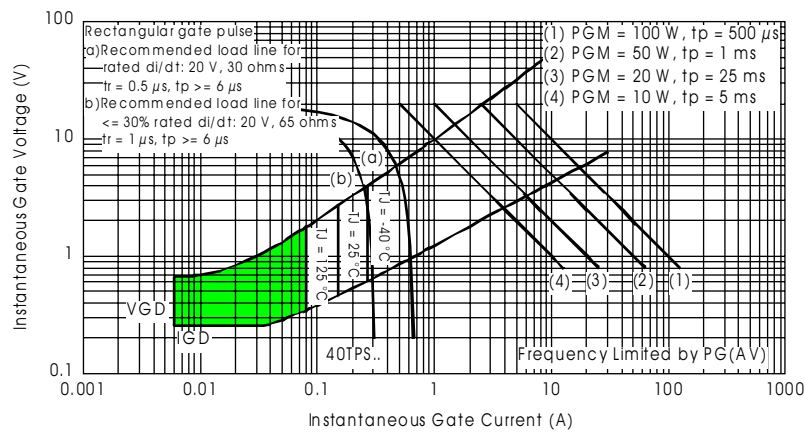


Fig. 8 - Gate Characteristics

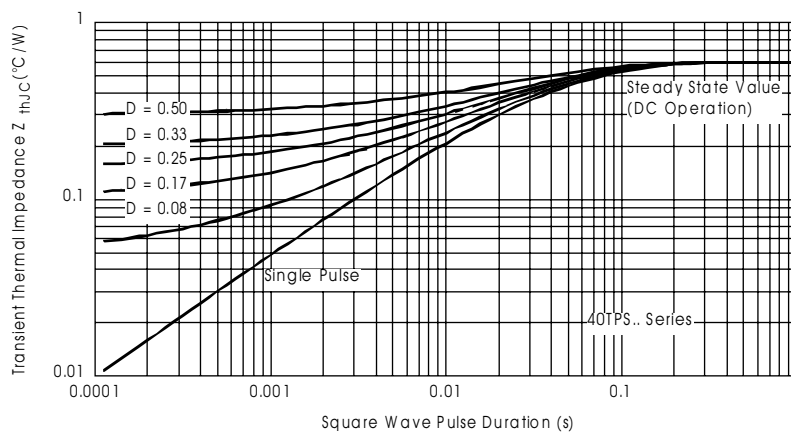


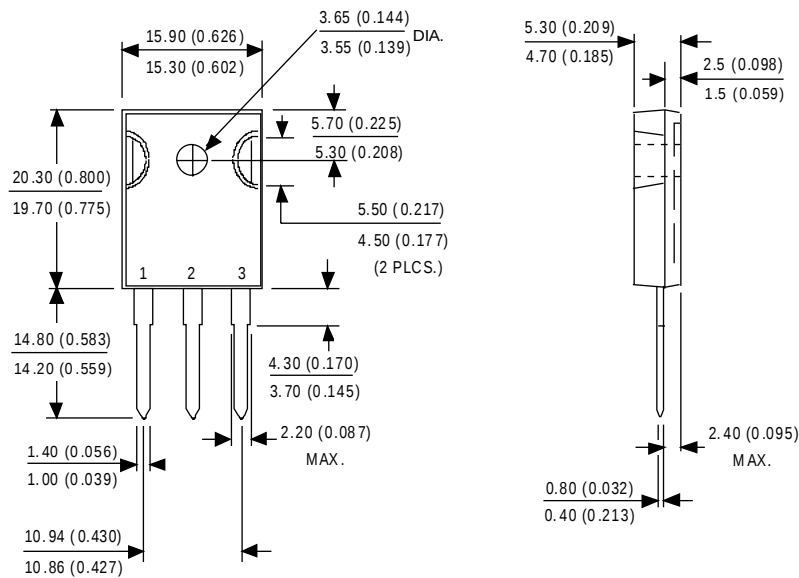
Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

40TPS.. *SAFEIR* Series

Bulletin I2107 rev. D 08/98

International
IR Rectifier

Outline Table



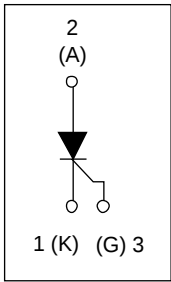
Dimensions in millimeters and inches

Ordering Information Table

Device Code

40	T	P	S	16	
①	②	③	④	⑤	⑥

- 1** - Current Rating
- 2** - Circuit Configuration:
T = Thyristor
- 3** - Package:
T = TO-247
- 4** - Type of Silicon:
S = Standard Recovery Rectifier
- 5** - Voltage code: Code x 100 = V_{RRM}
- 6** - None = Standard Igt selection
A = Low Igt selection 40mA max. only for 40TPS08A



08	= 800V
12	= 1200V
16	= 1600V